

Low-threshold optical bistabilities in ultra-thin plasmonic films

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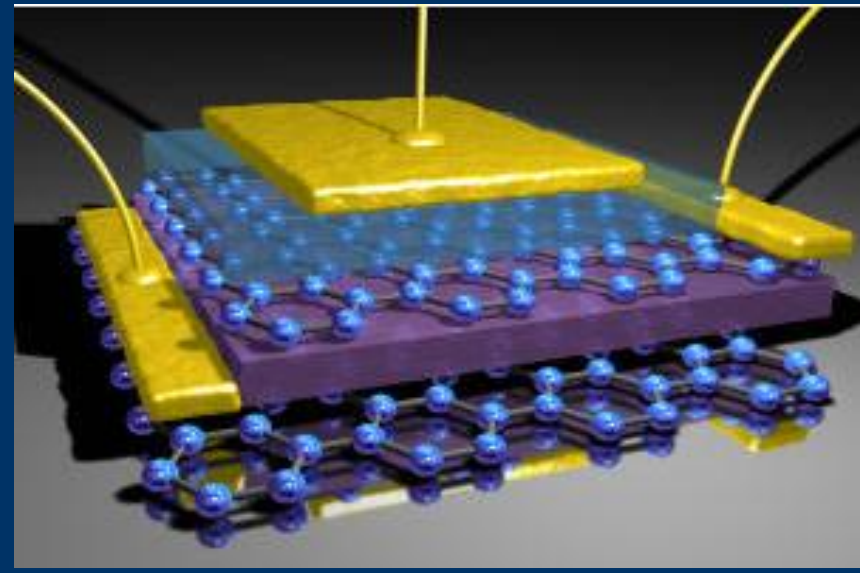
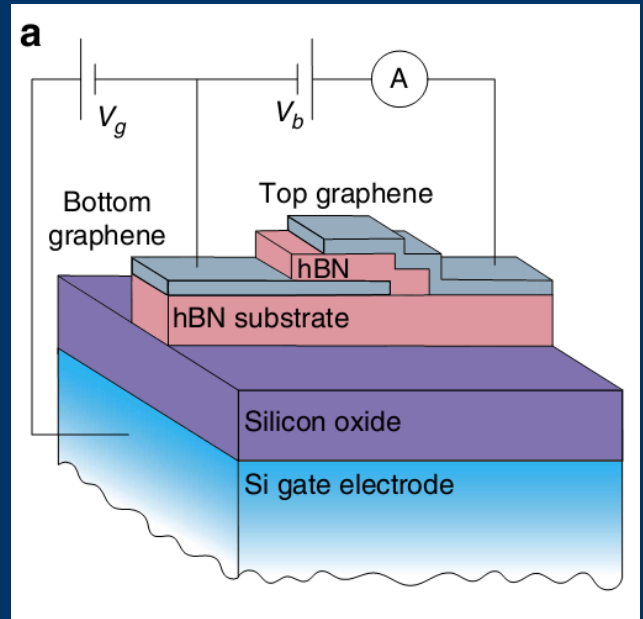
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Backgrounds:

Optical bistability can be used as optical switching, optical memories, optical transistors, optical diode, and optical computing.



Problem:

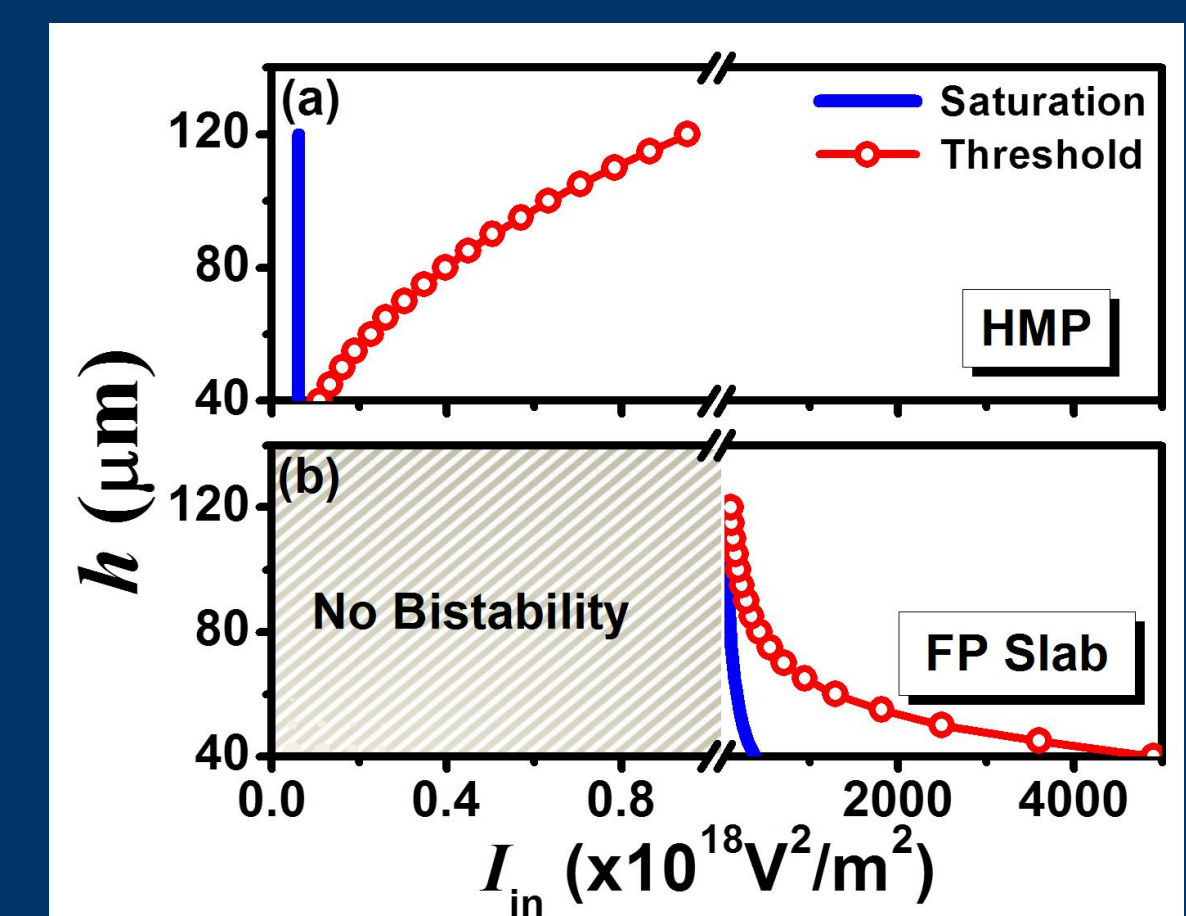
- Incident light needs high power
- Devices must be comparable to wavelength to sustain a FP mode

Motivation:

- A new mechanism to achieve OB at low input power
- Device with a miniaturized size

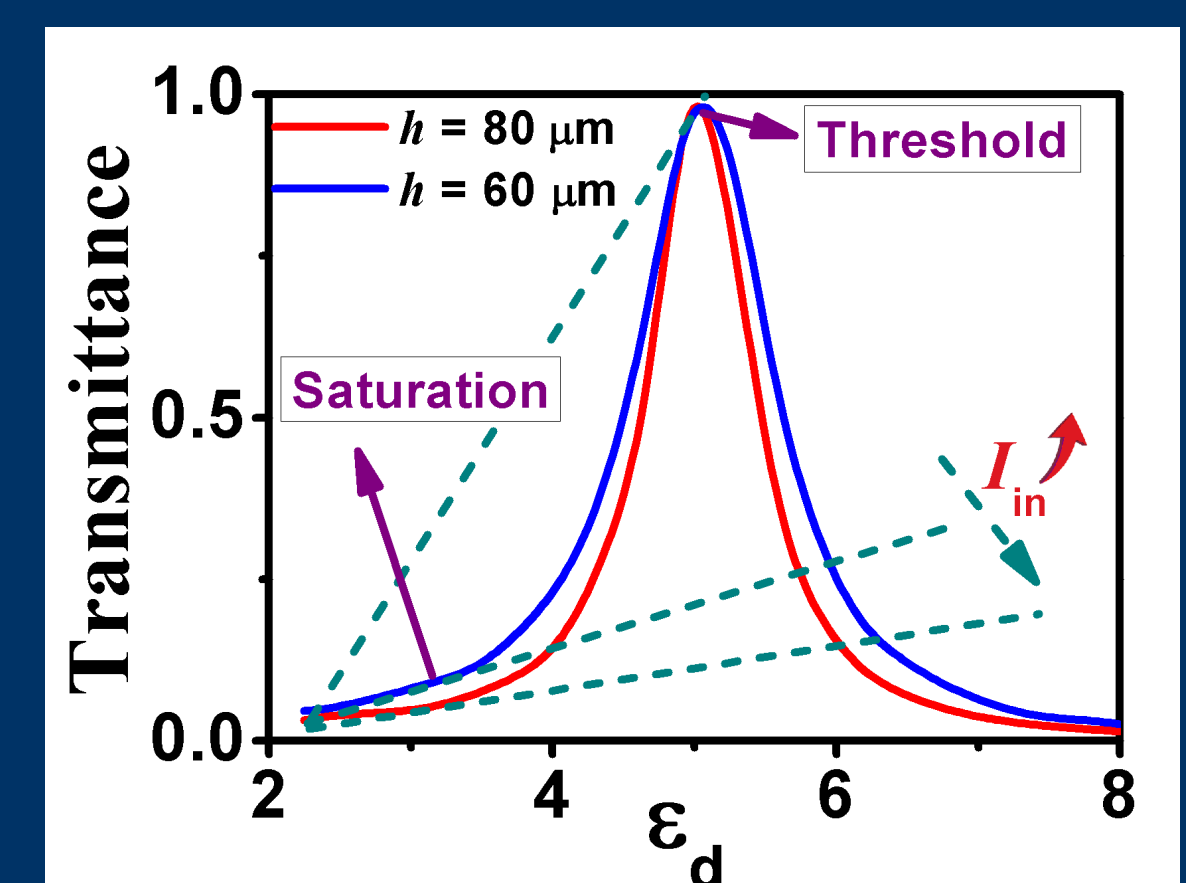
Discussions:

Film-thickness dependences of the threshold field and saturation field



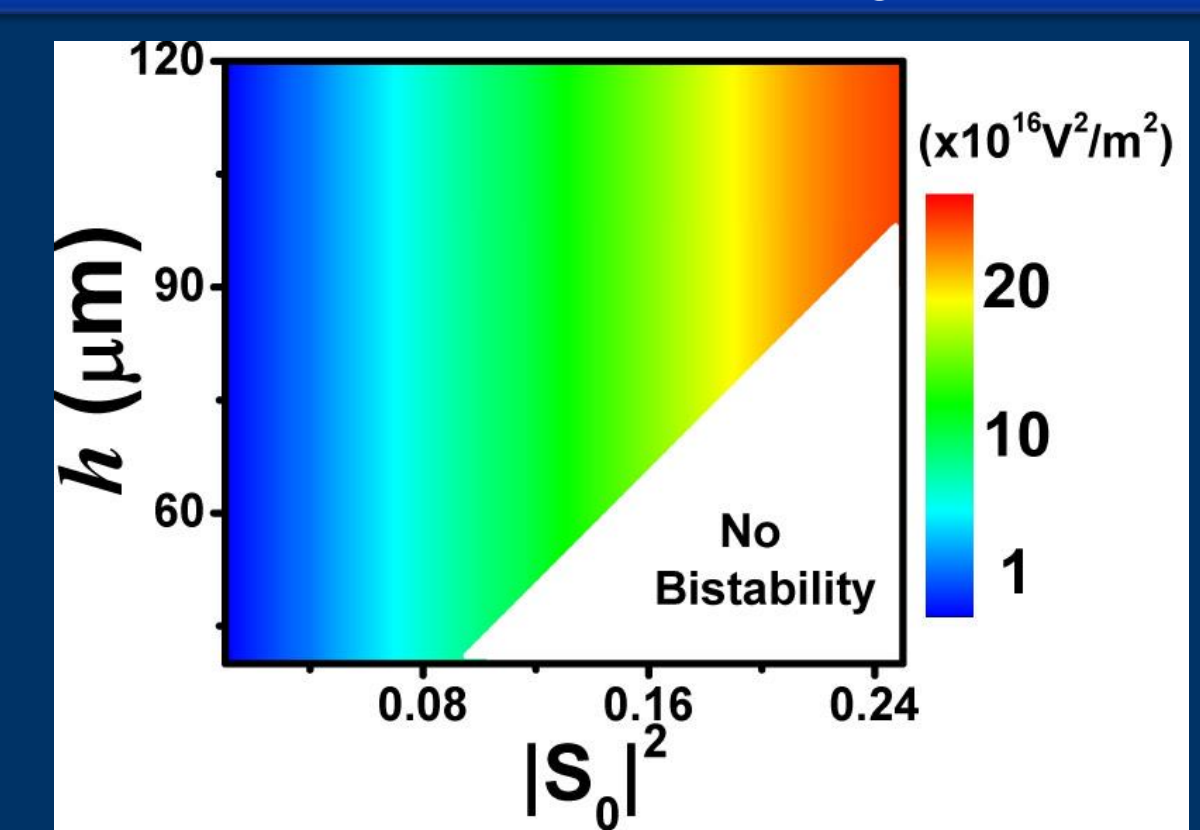
- Threshold of HMP much smaller than FP slab
- Mechanism is different: k=0 mode and field enhance

OB threshold and saturation fields in systems with different thicknesses



- Transmission peaks insensitive to film thickness h
- Transmission peak is narrowed when h is increased

Threshold versus S₀ and h

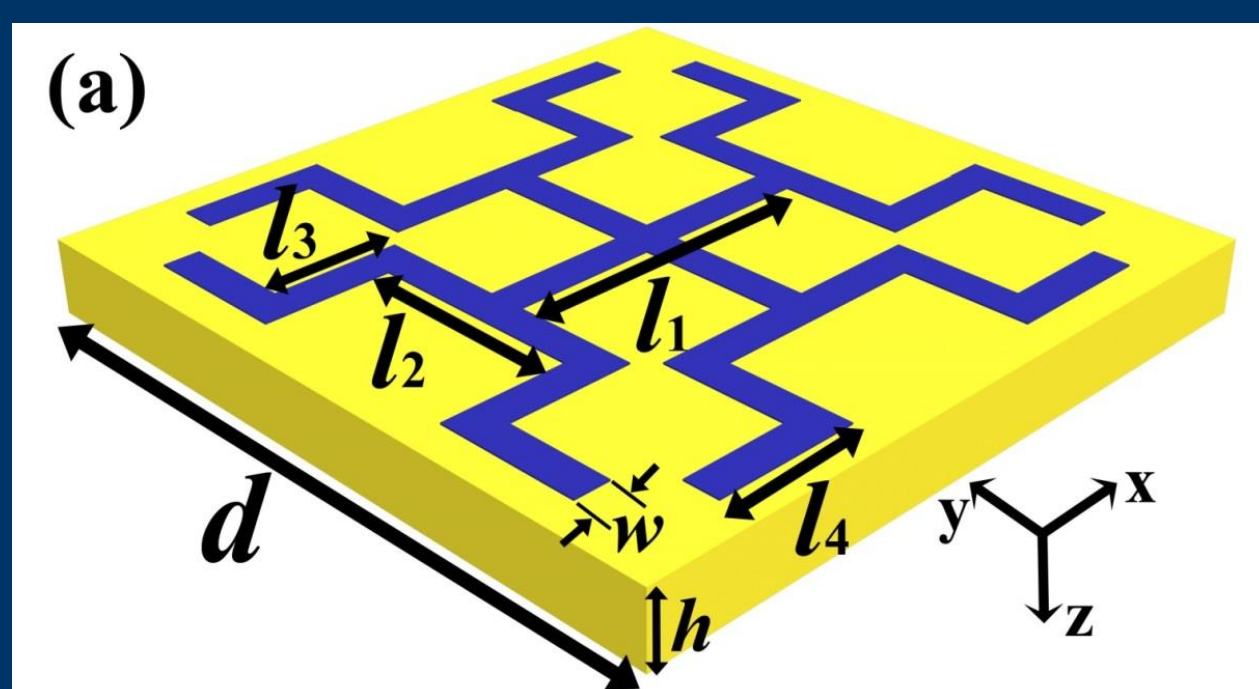


- Threshold decreases when S₀ becomes smaller
- Threshold is independent on h

Conclusions:

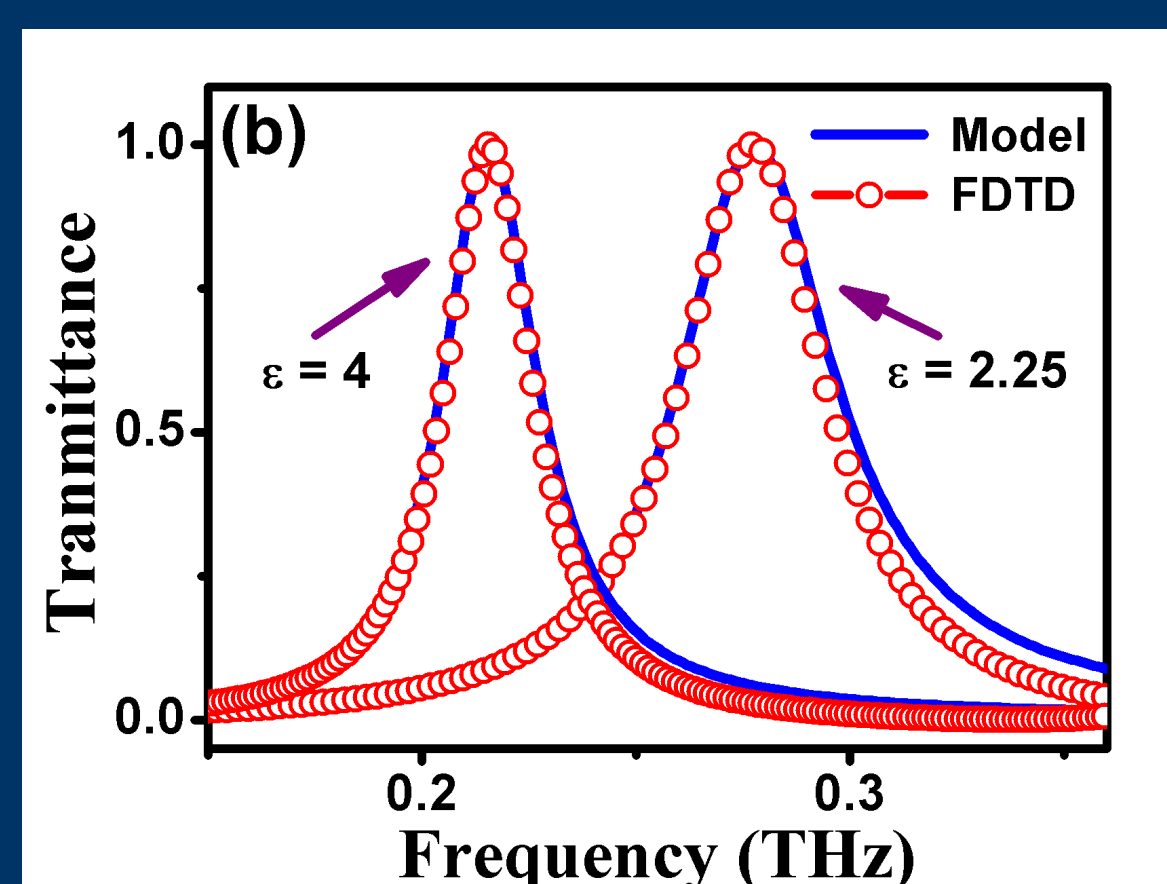
- Ultra-low bistability threshold ($4.85 \times 10^{16} \text{ V}^2/\text{m}^2$) that is 3500 times smaller than conventional optical bistable device
- Operation in a wavelength of 1500 micron (~0.2 THz), the thickness of the device can be as thin as 60 microns (1/25 of the wavelength)
- Device supports an operating bandwidth of 19 GHz

Linear results:



Schematic of the holey metallic plate (HMP) device

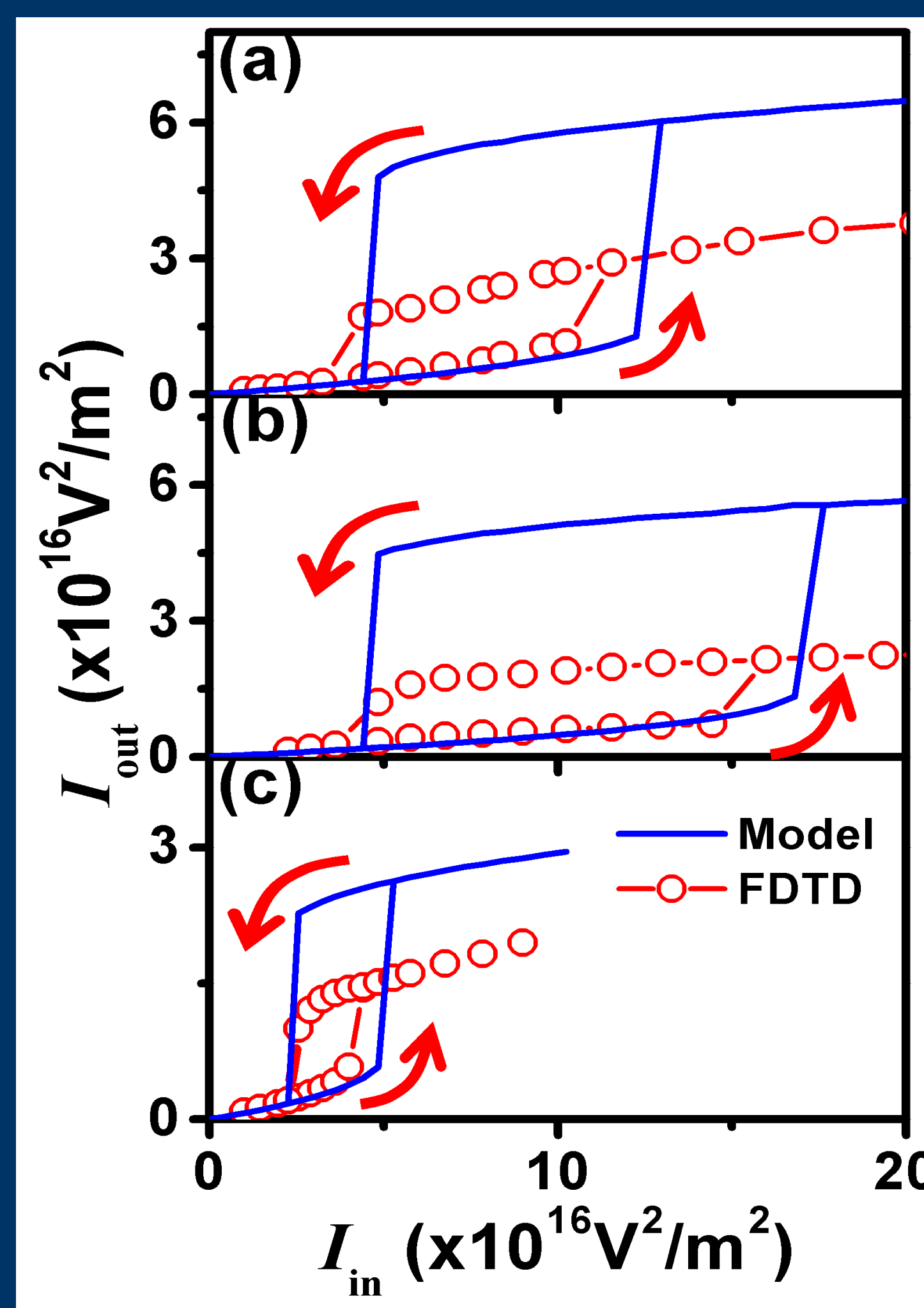
Yellow region: metal
Blue region: Kerr material



Transmission spectra

- Red shift when dielectric of Kerr material increases
- FDTD calculation agrees with Model calculation

Nonlinear results:



w = 20 μm

h = 60 μm

w = 20 μm

h = 80 μm

w = 15 μm

h = 60 μm

- ◆ Thickness is only 1/25 of the wavelength
- ◆ Threshold independent of the film thickness
- ◆ Saturation increases when h increased
- ◆ Strongly depend on width of the aperture
- ◆ Difference between FDTD and model because of self-phase modulation

Model calculation

Linear transmittance at normal incidence

$$T = \left| \frac{4Y_0 Y_{\text{hole}} e^{iq_z h}}{(Y_0 + Y_{\text{hole}})^2 - (Y_0 - Y_{\text{hole}})^2 e^{2iq_z h}} \right|^2$$

$$\varepsilon_d = 2.25 + \chi^{(3)} \cdot \frac{A_{\text{u.c.}}}{A_{\text{hole}}} \cdot \frac{|\vec{E}_0|^2 \cdot T}{|S_0|^2}$$

- Permittivity of the Kerr medium
- E field enhanced by the area correction and $(1/S_0)^2$

$$S_0 = \frac{\int_{\text{hole}} (\vec{E}^{\text{inc}})^* \cdot (\vec{E}^{\text{wg}}) dx dy}{\sqrt{\int_{\text{unit cell}} |\vec{E}^{\text{inc}}|^2 dx dy} \cdot \int_{\text{hole}} |\vec{E}^{\text{wg}}|^2 dx dy}$$

- S₀: Overlapping integral between incident wave & fundamental waveguide mode
- S₀: Characterizes the Q-factor and field enhancement inside the aperture

References:

1. W. Chen, and D. L. Mills, Phys. Rev. B **35**, 524 (1987).
2. S. W. Tang, B. C. Zhu, S. Y. Xiao, J. T. Shen and L. Zhou, Opt. Lett. **39**, 3213 (2014)

